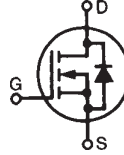


TrenchHV™ Power MOSFET

IXTH102N20T
IXTQ102N20T
IXTV102N20T

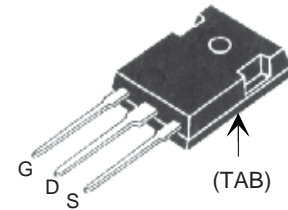
$V_{DSS} = 200 \text{ V}$
 $I_{D25} = 102 \text{ A}$
 $R_{DS(on)} \leq 23 \text{ m}\Omega$

N-Channel Enhancement Mode
Avalanche Rated

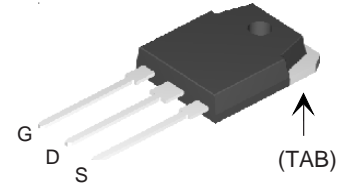


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 175°C	200	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	102	A
I_{LRMS}	Lead Current Limit, RMS	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	250	A
I_{AS}	$T_C = 25^\circ\text{C}$	5	A
E_{AS}	$T_C = 25^\circ\text{C}$	1.2	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A/ms}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 175^\circ\text{C}$, $R_G = 2.5 \Omega$	7	V/ns
P_D	$T_C = 25^\circ\text{C}$	750	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ\text{C}$
M_d	Mounting torque (TO-247 & TO-3P)	1.13 / 10	Nm/lb.in.
F_C	Mounting force (PLUS220)	11..65 / 2.5..14.6	N/lb.
Weight	TO-247	6	g
	TO-3P	5.5	g
	PLUS220	4	g

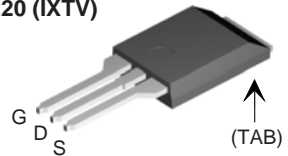
TO-247 (IXTH)



TO-3P (IXTQ)



PLUS220 (IXTV)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			5 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$, Notes 1, 2	18		23 $\text{m}\Omega$

Features

- Unclamped Inductive Switching (UIS) rated
- Low package inductance - easy to drive and to protect
- 175 $^\circ\text{C}$ Operating Temperature

Advantages

- Easy to mount
- Space savings
- High power density

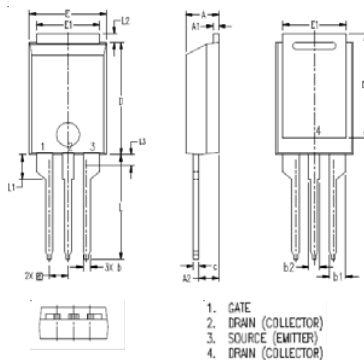
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$, Note 1	55	92	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		6800	pF
C_{oss}			722	pF
C_{rss}			126	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2.5\ \Omega$ (External)		19	ns
t_r			26	ns
$t_{d(off)}$			50	ns
t_f			25	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 25\text{ A}$		114	nC
Q_{gs}			34	nC
Q_{gd}			31	nC
R_{thJC}			0.25	$^\circ\text{C/W}$
R_{thCS}				$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			102 A
I_{SM}	Pulse width limited by T_{JM}			330 A
V_{SD}	$I_F = 50\text{ A}, V_{GS} = 0\text{ V}$, Note 1			1.2 V
t_{rr}	$I_F = 50\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 50\text{ V}, V_{GS} = 0\text{ V}$		130	ns

- Notes: 1. Pulse test, $t \leq 300\text{ ms}$, duty cycle, $d \leq 2\%$;
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5 mm or less from the package body.

PLUS220 (IXTV) Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.028	.035	0.70	0.90
A2	.098	.118	2.50	3.00
b	.035	.047	0.90	1.20
b1	.080	.095	2.03	2.41
b2	.054	.064	1.37	1.63
c	.028	.035	0.70	0.90
D	.551	.591	14.00	15.00
D1	.512	.539	13.00	13.70
E	.394	.433	10.00	11.00
E1	.331	.346	8.40	8.80
e	.100 BSC		2.54 BSC	
L	.512	.551	13.00	14.00
L1	.118	.138	3.00	3.50
L2	.035	.051	0.90	1.30
L3	.047	.059	1.20	1.50

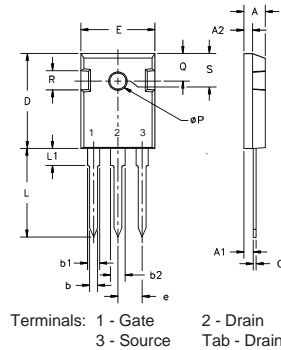
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

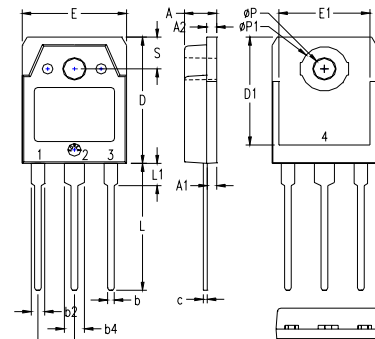
TO-247AD Outline



Terminals: 1 - Gate 2 - Drain 3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A1	2.2	2.54	.087	.102
A2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b1	1.65	2.13	.065	.084
b2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1	4.50		.177	
ÆP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC	242 BSC		

TO-3P (IXTQ) Outline



Pins: 1 - Gate 2 - Drain 3 - Source 4, TAB - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
ØP	.126	.134	3.20	3.40
ØP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

All metal area are tin plated.

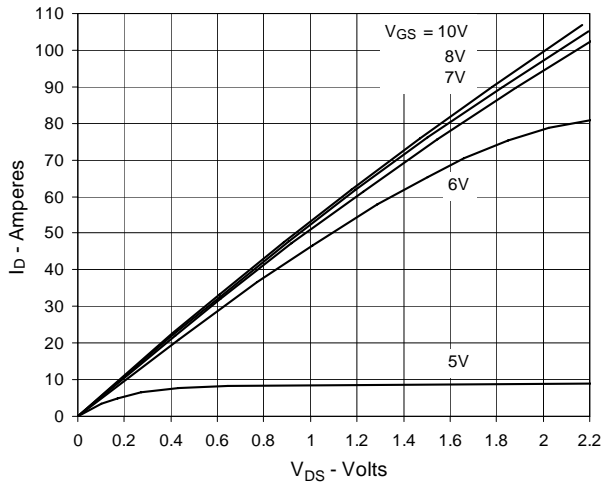
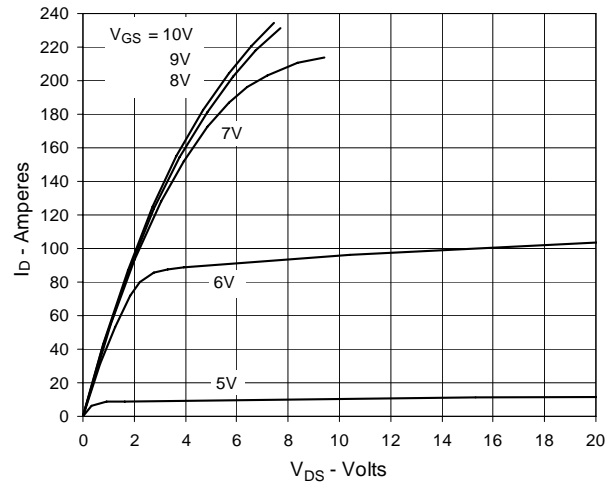
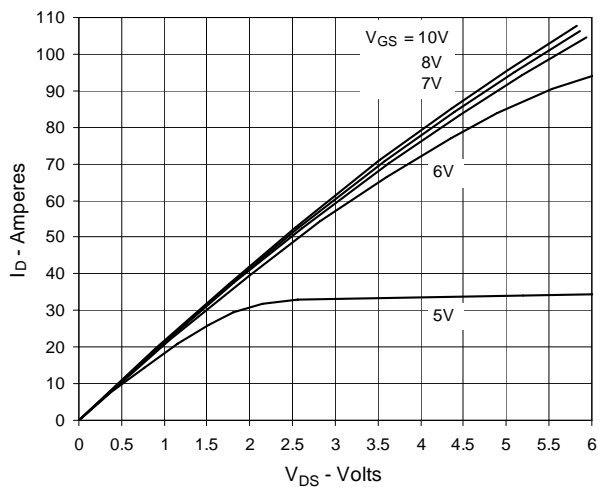
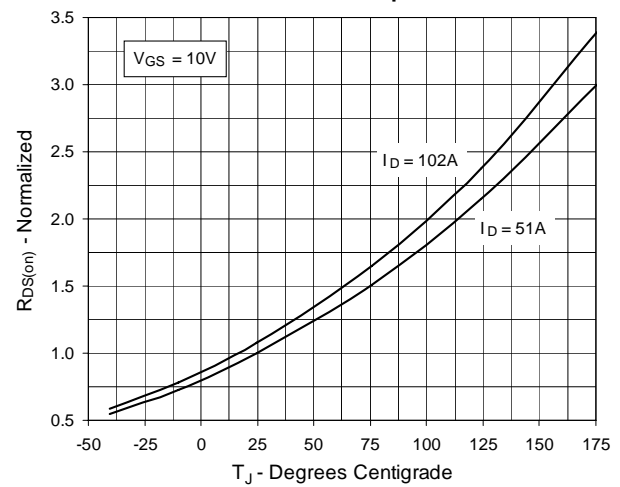
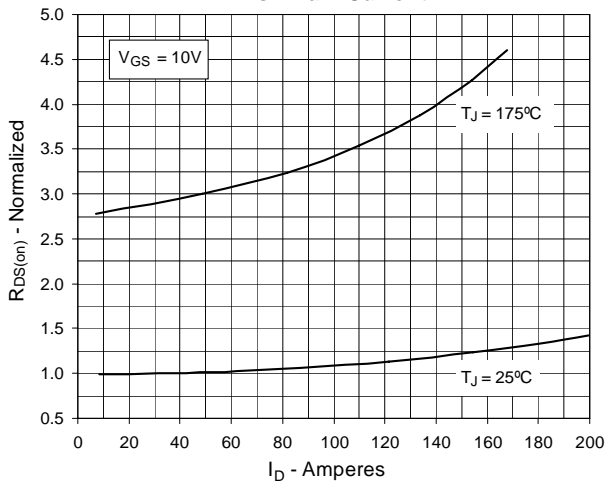
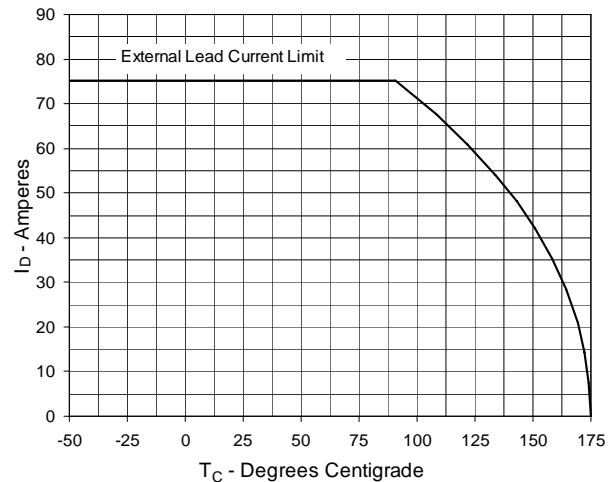
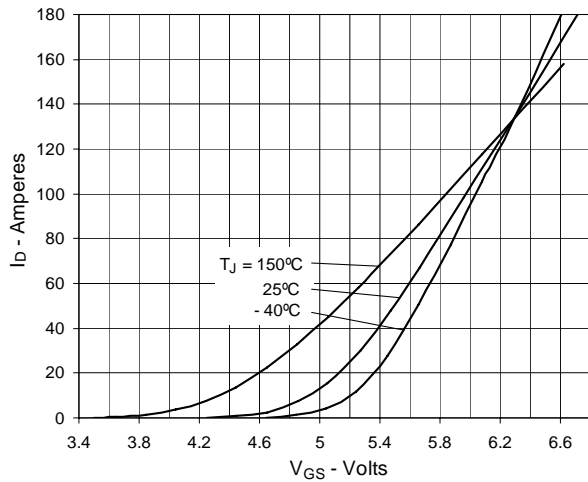
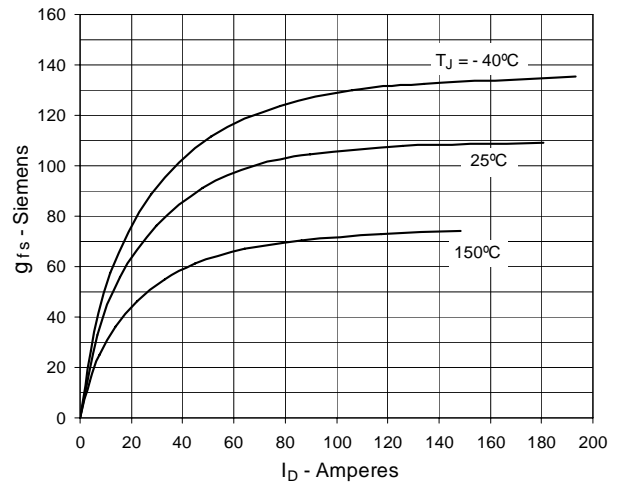
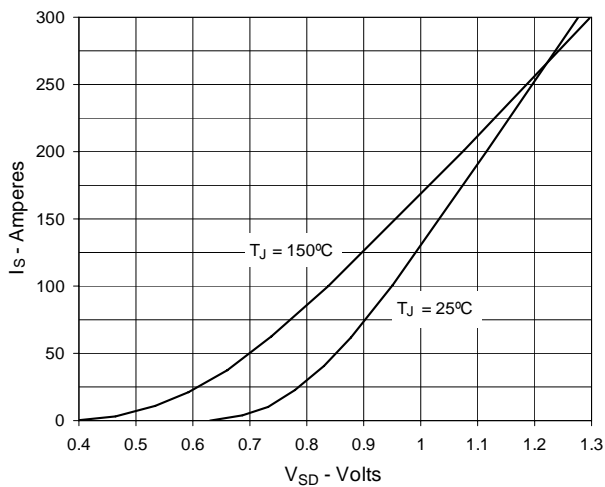
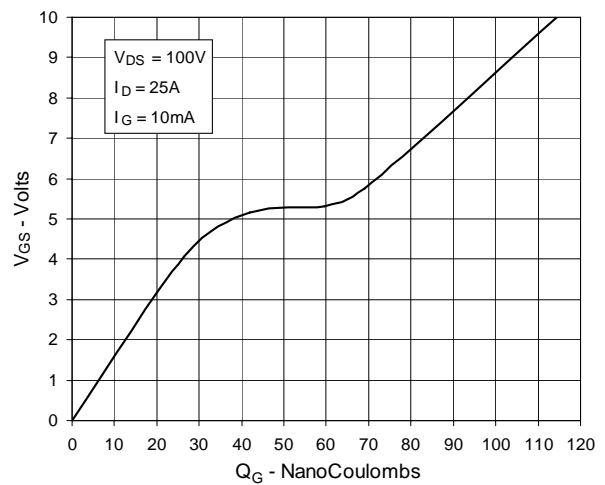
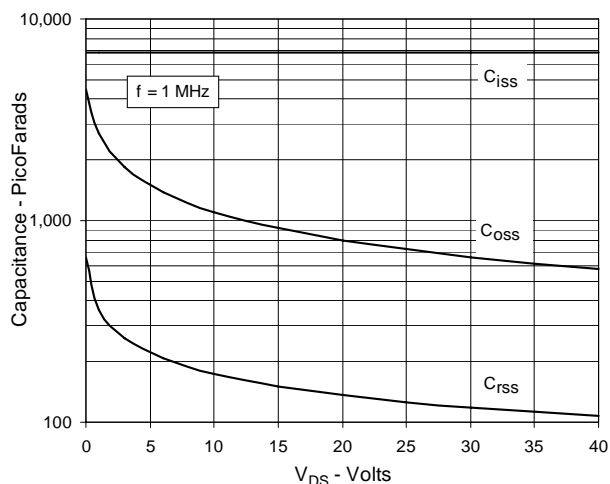
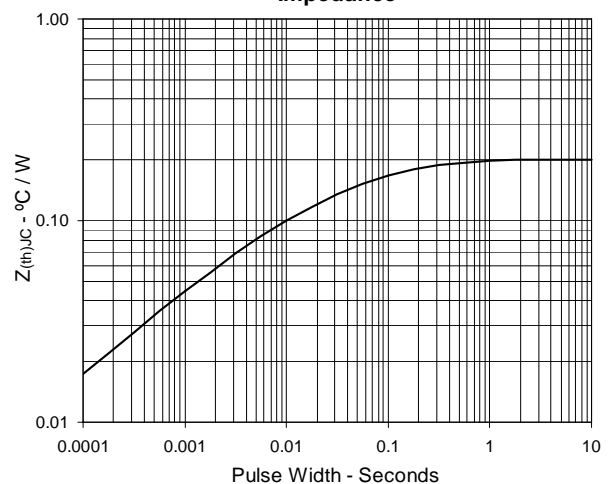
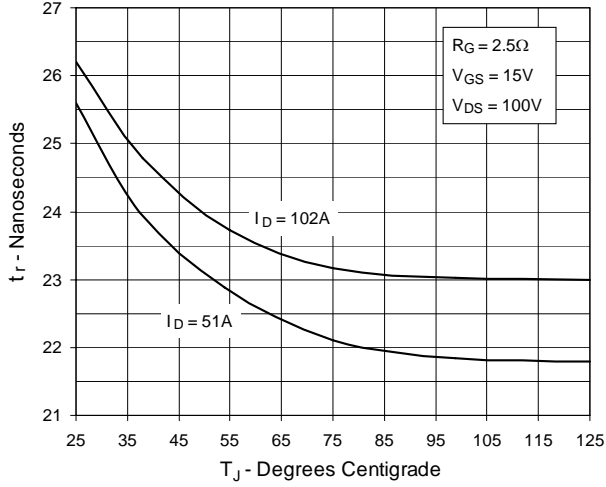
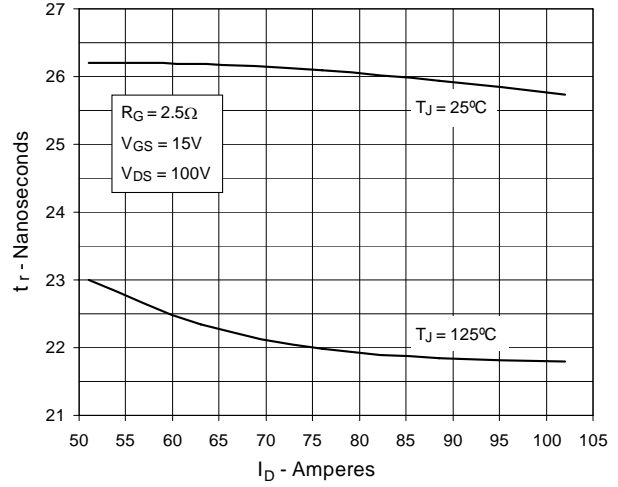
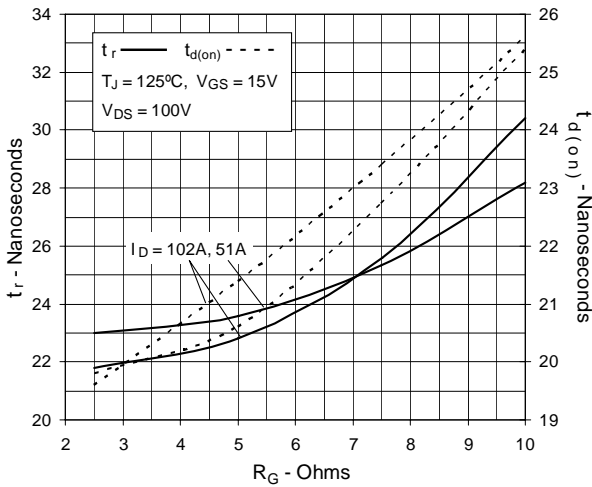
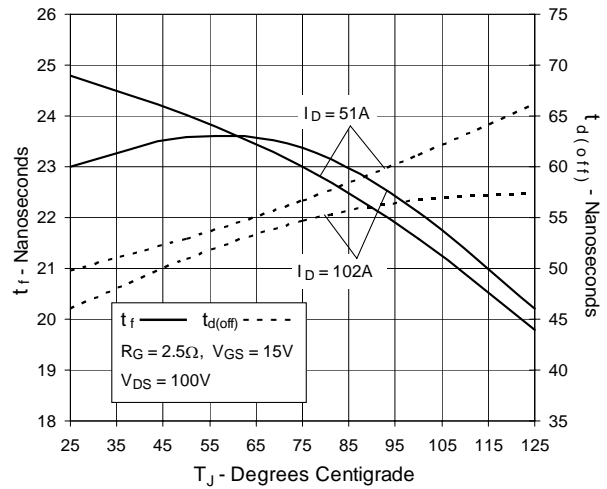
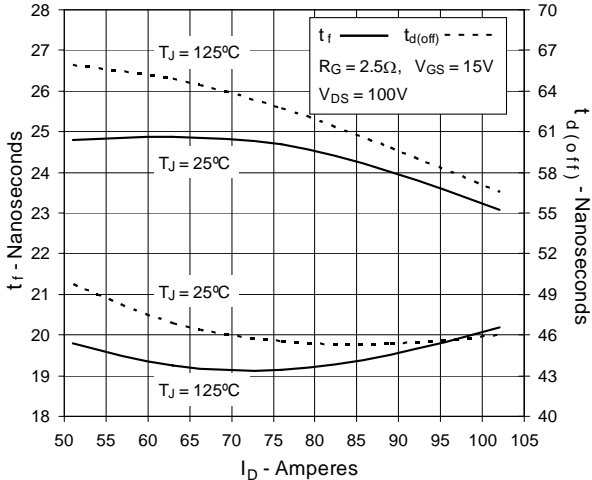
Fig. 1. Output Characteristics @ 25°C

Fig. 2. Extended Output Characteristics @ 25°C

Fig. 3. Output Characteristics @ 150°C

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 51A$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 51A$ Value vs. Drain Current

Fig. 6. Drain Current vs. Case Temperature


Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance


**Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature**

**Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current**

**Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance**

**Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature**

**Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current**

**Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance**
